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ESD Protection Diode

Dual Line Automotive Bus Protector

NUP2125, SZNUP2125

The SZ/NUP2125 has been designed to protect both CAN and LIN transceivers from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SC-70 (SOT-323) package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

Features

- 200 W Peak Power Dissipation per Line (8/20 μ s Waveform)
- Diode Capacitance Matching
- Low Reverse Leakage Current (< 100 nA)
- IEC Compatibility:
 - IEC 61000-4-2 (ESD): Level 4
 - IEC 61000-4-4 (EFT): 50 A – 5/50 ns
 - IEC 61000-4-5 (Lighting) 3.0 A (8/20 μ s)
- ISO 7637-1, Nonrepetitive EMI Surge Pulse 2, 8.0 A (1/50 μ s)
- ISO 7637-3, Repetitive Electrical Fast Transient (EFT) EMI Surge Pulses, 50 A (5/50 ns)
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

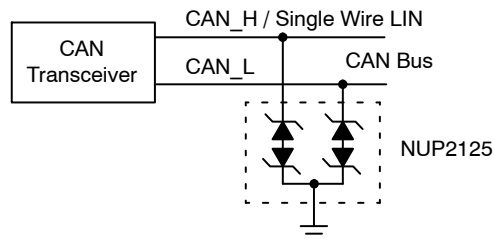
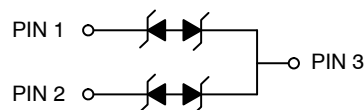
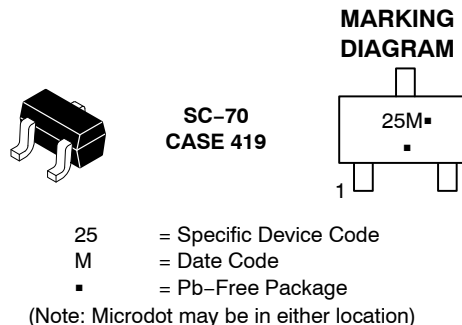
Applications

- Automotive Networks
 - ◆ CAN / CAN-FD
 - ◆ Low and High-Speed CAN
 - ◆ Fault Tolerant CAN
 - ◆ LIN



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ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NUP2125, SZNUP2125

MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation, 8/20 μs Double Exponential Waveform (Note 1)	200	W
T _J	Operating Junction Temperature Range	-55 to 150	°C
T _J	Storage Temperature Range	-55 to 150	°C
T _L	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM)	±8.0	kV
	Machine Model (MM)	±1.6	kV
	IEC 61000-4-2 Contact	±30	kV
	IEC 61000-4-2 Air	±30	kV
	ISO 10605 150 pF / 2 kΩ Contact	±30	kV
	ISO 10605 330 pF / 2 kΩ Contact	±30	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 1.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	(Note 2)	24	-	-	V
V _{BR}	Breakdown Voltage	I _T = 1 mA (Note 3)	27	28.5	32	V
I _R	Reverse Leakage Current	V _{RWM} = 24 V	-	15	100	nA
V _C	Clamping Voltage	I _{PP} = 1 A (8/20 μs Waveform) (Note 4)	-	33.4	36.6	V
V _C	Clamping Voltage	I _{PP} = 3 A (8/20 μs Waveform) (Note 4)	-	44	50	V
I _{PP}	Maximum Peak Pulse Current	8/20 μs Waveform (Note 4)	-	-	3.0	A
C _J	Capacitance	V _R = 0 V, f = 1 MHz (Line to GND)	-	7.0	10	pF
		V _R = 5 V, f = 1 MHz (Line to GND)	-	4.5	6.0	pF
		V _R = 5 V, f = 1 MHz (Line to GND), T _A = +150°C	-	5.0	-	pF
ΔC	Diode Capacitance Matching	V _R = 0 V, 5 MHz (Note 5)	-	0.26	2	%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
3. V_{BR} is measured at pulse test current I_T.
4. Pulse waveform per Figure 1.
5. ΔC is the percentage difference between C_J of lines 1 and 2 measured according to the test conditions given in the electrical characteristics table.

ORDERING INFORMATION

Device	Package	Shipping [†]
NUP2125WTT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
SZNUP2125WTT1G*		
NUP2125WTT3G		10000 / Tape & Reel
SZNUP2125WTT3G*		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

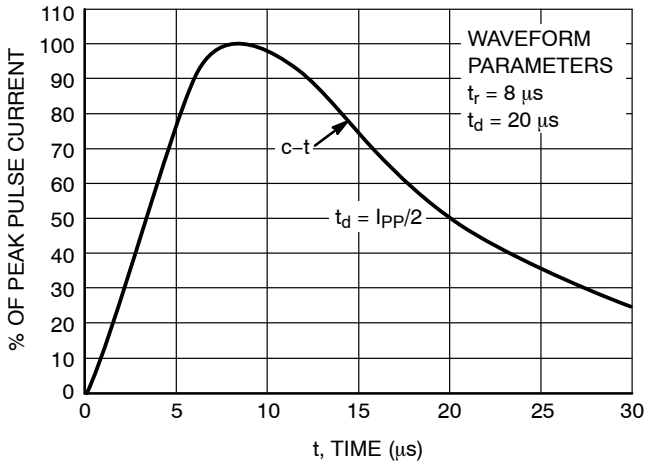


Figure 1. Pulse Waveform, $8 \times 20 \mu\text{s}$

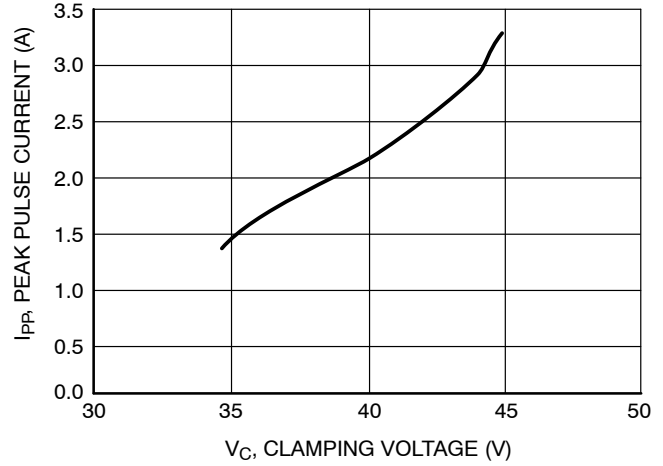


Figure 2. Clamping Voltage vs Peak Pulse Current

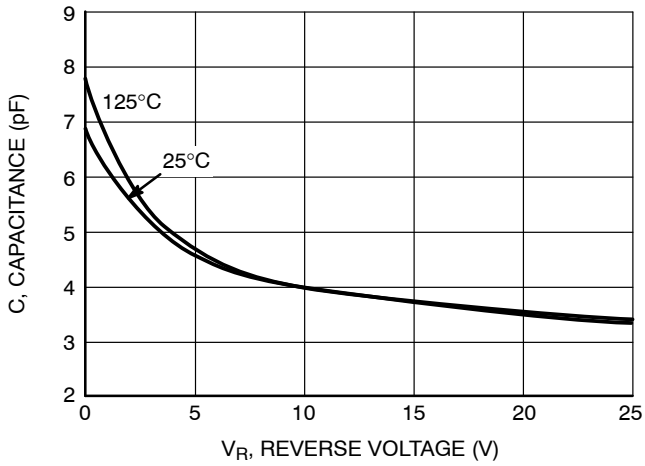


Figure 3. Typical Junction Capacitance vs Reverse Voltage

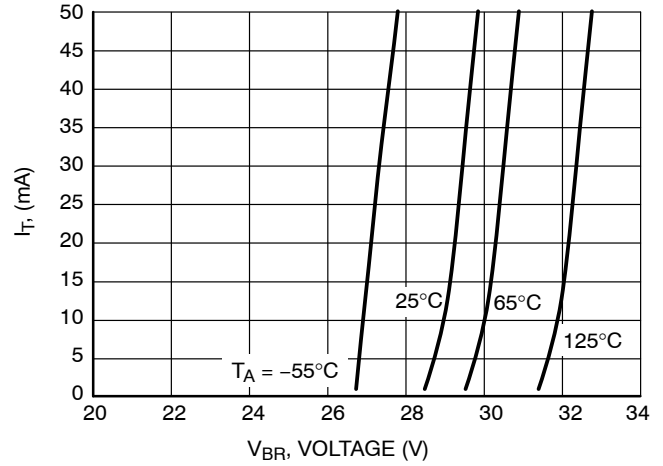


Figure 4. V_{BR} versus I_T Characteristics

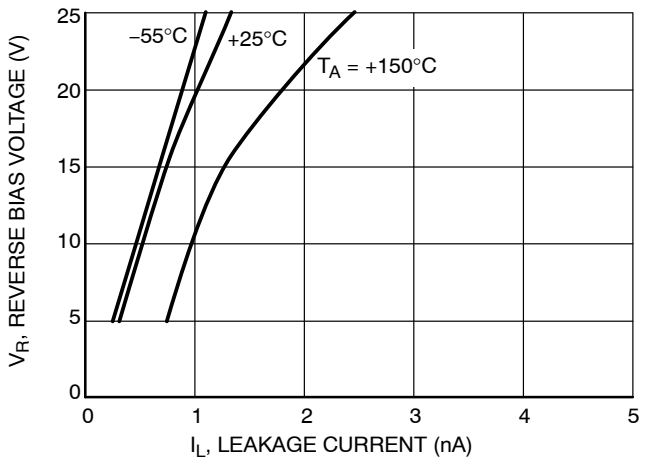


Figure 5. I_R versus Temperature Characteristics

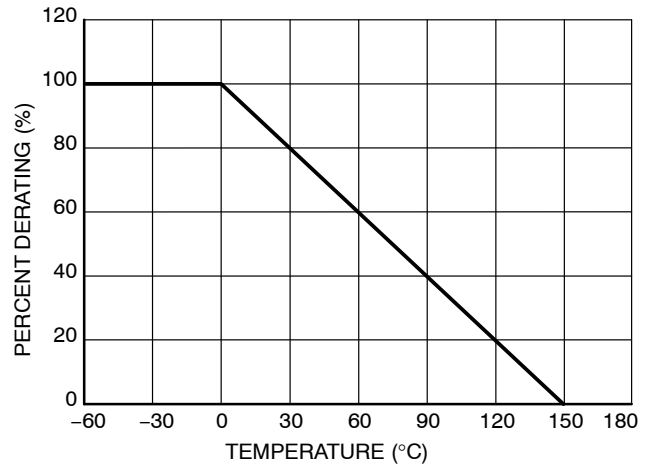


Figure 6. Temperature Power Dissipation Derating

NUP2125, SZNUP2125

Surge Protection Diode Circuit

Surge protection diodes provide protection to a transceiver by clamping a surge voltage to a safe level. Surge protection diodes have high impedance below and low impedance above their breakdown voltage. A surge protection Zener diode has its junction optimized to absorb the high peak energy of a transient event, while a standard Zener diode is designed and specified to clamp a steady state voltage.

Figure 7 provides an example of a dual bidirectional surge protection diode array that can be used for protection with the high-speed CAN network. The bidirectional array is created from four identical Zener TVS diodes. The clamping voltage of the composite device is equal to the

breakdown voltage of the diode that is reversed biased, plus the diode drop of the second diode that is forward biased.

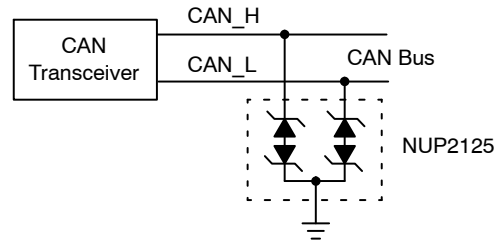


Figure 7. High-Speed and Fault Tolerant CAN Surge Protection Circuit